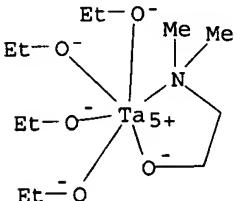


L7 ANSWER 1 OF 18 HCPLUS COPYRIGHT 2003 ACS on STN
 AN 2003:297795 HCPLUS
 DN 138:279838
 TI Manufacturing method for dielectric layer of capacitor
 IN Huang, Guo-Tai; You, Tsuei-Rung
 PA United Microelectronics Corp., Taiwan
 SO Taiwan, 17 pp.
 CODEN: TWXXA5
 DT Patent
 LA Chinese
 IC ICM H01L021-8242
 ICS H01L021-76
 CC 76-10 (Electric Phenomena)
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	TW 410441	B	20001101	TW 1999-88110830	19990628
PRAI	TW 1999-88110830				
AB	Organometallic precursor for depositing Ta oxide dielec. layer on elec. capacitor is described. The single phase Ta oxide dielec. layers are formed by MOCVD. The dielec. const. of the dielec. layer can be adjusted by adjusting the compn. of the precursor. The process is used for the fabrication of DRAM memories.				
IT	1314-61-0P, Tantalum oxide Ta205 RL: DEV (Device component use); PNU (Preparation, unclassified); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (MOCVD with organometallic precursor for dielec. layer of capacitor for DRAM device fabrication)				
IT	6074-84-6, Tantalum pentaethoxide 169896-41-7 172901-22-3 177580-52-8 177580-53-9 238757-13-6 RL: RCT (Reactant); RACT (Reactant or reagent) (MOCVD with organometallic precursor for dielec. layer of capacitor for DRAM device fabrication)				
IT	172901-22-3 177580-52-8 177580-53-9 238757-13-6 RL: RCT (Reactant); RACT (Reactant or reagent) (MOCVD with organometallic precursor for dielec. layer of capacitor for DRAM device fabrication)				
RN	172901-22-3 HCPLUS				
CN	Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)				



RN 177580-52-8 HCPLUS
 CN Tantalum, tetraethoxy(2,2,6,6-tetramethyl-3,5-heptanedionato-.kappa.O,.kappa.O')-, (OC-6-22)- (9CI) (CA INDEX NAME)